

CTLT953-M833

**SURFACE MOUNT
HIGH CURRENT
PNP SILICON TRANSISTOR**



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DESCRIPTION:

The CENTRAL SEMICONDUCTOR CTLT953-M833 is a high performance 5.0A High Current PNP Transistor designed for applications where small size and operational efficiency are prime requirements. With a maximum power dissipation of 4.5W, and a very small package footprint, this device is 80% smaller than a comparable SOT-223 device. This leadless package design has a watts per unit area at least twice that of equivalent package devices.

MARKING CODE: CHA4

- NPN Complement: CTLT853-M833

FEATURES:

- High Voltage (140V)
- High Thermal Efficiency
- High Current ($I_C=5.0A$)
- 3 x 3mm TLM™ case
- Low $V_{CE(SAT)} = 420mV$ MAX @ 4.0A

MAXIMUM RATINGS: ($T_A=25^\circ C$)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	140	V
Collector-Emitter Voltage	V_{CEO}	100	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Continuous Collector Current	I_C	5.0	A
Power Dissipation (Note 1)	P_D	4.5	W
Power Dissipation (Note 2)	P_D	4.0	W
Power Dissipation (Note 3)	P_D	2.5	W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ C$
Thermal Resistance (Note 1)	θ_{JA}	27.78	$^\circ C/W$
Thermal Resistance (Note 2)	θ_{JA}	31.25	$^\circ C/W$
Thermal Resistance (Note 3)	θ_{JA}	50.00	$^\circ C/W$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ C$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{CBO}	$V_{CB}=100V$			50	nA
I_{CBO}	$V_{CB}=100V, T_A=100^\circ C$			1.0	μA
I_{CER}	$V_{CE}=100V, R_{BE} \leq 1.0k\Omega$			50	nA
I_{EBO}	$V_{EB}=6.0V$			10	nA
BV_{CBO}	$I_C=100\mu A$	140	170		V
BV_{CER}	$I_C=10mA, R_{BE} \leq 1.0k\Omega$	140	150		V
BV_{CEO}	$I_C=10mA$	100	120		V
BV_{EBO}	$I_E=100\mu A$	6.0	9.0		V
$V_{CE(SAT)}$	$I_C=100mA, I_B=10mA$		20	50	mV
$V_{CE(SAT)}$	$I_C=1.0A, I_B=100mA$		90	120	mV
$V_{CE(SAT)}$	$I_C=2.0A, I_B=200mA$		170	220	mV
$V_{CE(SAT)}$	$I_C=4.0A, I_B=400mA$		320	420	mV
$V_{BE(SAT)}$	$I_C=4.0A, I_B=400mA$		1.0	1.2	V

- Notes: (1) Ceramic or aluminum core PC Board with copper mounting pad area of 75 mm²
 (2) FR-4 Epoxy PC Board with copper mounting pad area of 75 mm²
 (3) FR-4 Epoxy PC Board with copper mounting pad area of 25 mm²

R1 (17-February 2010)

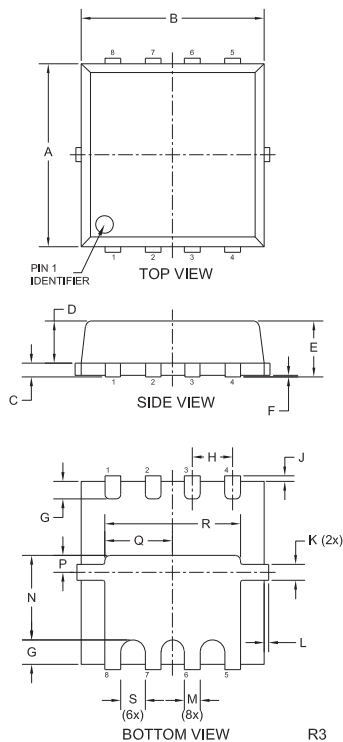
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ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
h_{FE}	$V_{CE}=1.0V, I_C=10mA$	100			
h_{FE}	$V_{CE}=1.0V, I_C=1.0A$	100	200	300	
h_{FE}	$V_{CE}=1.0V, I_C=3.0A$	50	70		
h_{FE}	$V_{CE}=1.0V, I_C=4.0A$	30	45		
h_{FE}	$V_{CE}=1.0V, I_C=10A$		15		
f_T	$V_{CE}=10V, I_C=100mA, f=50MHz$		150		MHz
C_{ob}	$V_{CB}=10V, I_E=0, f=1.0MHz$		45		pF

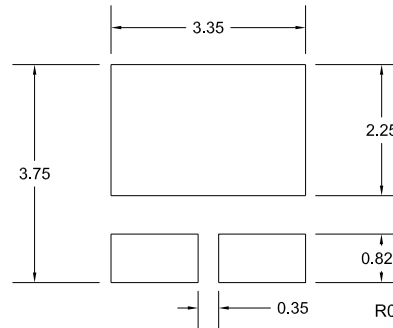
TLM833 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.114	0.122	2.90	3.10
B	0.114	0.122	2.90	3.10
C	0.006	0.010	0.15	0.25
D	0.026	0.030	0.65	0.75
E	0.031	0.039	0.80	1.00
F	0.000	0.002	0.00	0.05
G	0.008	0.018	0.20	0.45
H	0.026		0.65	
J	---	0.005	---	0.125
K	0.007	0.012	0.17	0.30
L	---	0.005	---	0.125
M	0.011	0.015	0.29	0.39
N	0.049	0.057	1.25	1.45
P	0.006	0.014	0.15	0.35
Q	0.040	0.048	1.01	1.21
R	0.085	0.093	2.16	2.36
S	0.012	0.016	0.30	0.40

TLM833 (REV:R3)

REQUIRED MOUNTING PADS
(Dimensions in mm)



Failure to use this mounting pad layout may result in damage to device.

R1 (17-February 2010)